

No.3197

2SA1753/2SC4577

PNP/NPN Epitaxial Planar Silicon Transistors

Low-Frequency

General-Purpose Amp Applications

Features

- · Small-sized package permitting the 2SA1753/2SC4577-applied sets to be made small and slim.
- · Low collector-to-emitter saturation voltage.

():2SA1753

Absolute Maximum Ratings at	$Ta = 25^{\circ}C$		unit
Collector to Base Voltage	V_{CBO}	(-)20	V
Collector to Emitter Voltage	V_{CEO}	(-)15	V
Emitter to Base Voltage	$ m V_{EBO}$	(-)5	V
Collector Current	$I_{\mathbb{C}}$	(-)500	mA
Collector Current(Pulse)	I_{CP}	(-)1	Α
Collector Dissipation	$P_{\mathbf{C}}$	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	$^{\circ}\mathrm{C}$

Electrical Characteristics	at $Ta = 25^{\circ}C$		min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)15V, I_E = 0$			(-)0.1	μΑ
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE} = (-)2V, I_{C} = (-)10mA$	135%	K	600%	ĕ
	$h_{FE}(2)$	$V_{CE} = (-)2V, I_{C} = (-)400mA$	(70)80			
Gain-Bandwidth Product	$\mathbf{f_T}$	$V_{CE} = (-)2V_{IC} = (-)50mA$		300		MHz
				(400)		
Output Capacitance	c_{ob}	$V_{CB} = (-)10V, f = 1MHz$		(6.5)4.0		рF
C-E Saturation Voltage	$V_{CE(sat)}(1)$	$I_C = (-)5mA, I_B = (-)0.5mA$		(-)15	(-35)30	mV
	$V_{CE(sat)}(2)$	$I_C = (-)200 \text{mA}, I_B = (-)10 \text{mA}$		160	300	mV
				(-200)	(-360)	
B-E Saturation Voltage	$V_{\mathrm{BE}(\mathrm{sat})}$	$I_C = (-)200 \text{mA}, I_B = (-)10 \text{mA}$		(-)0.95	(-)1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_{\rm C} = (-)10 \mu {\rm A}, I_{\rm E} = 0$	(-)20			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1 \text{mA}, R_{BE} = \infty$	(-)15			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_{\rm E} = (-)10 \mu A, I_{\rm C} = 0$	(-)5			V

$\ensuremath{\texttt{\#}}$: The 2SA1753/2SC4577 are classified by 10mA h_{FE} as follows :

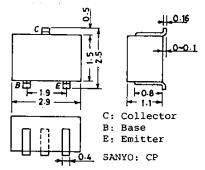
ľ	135	5	270	200	6	400	300	7	600
L							L		

Marking 2SA1753: ES 2SC4577: UT

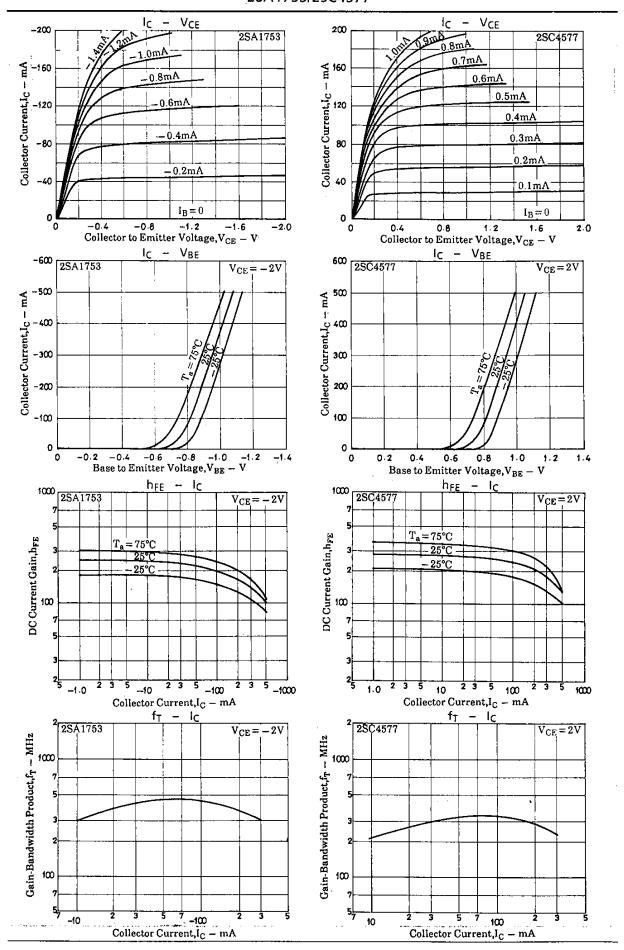
hFE rank: 5,6,7

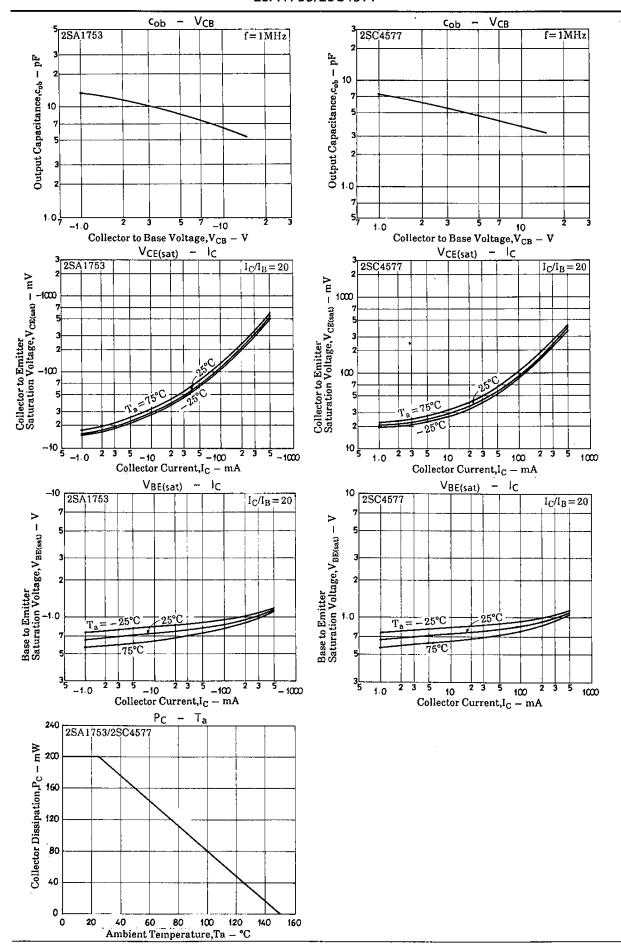
Package Dimensions 2018A

(unit: mm)



SANYO Electric Co., Ltd. Semiconductor Business Headquarters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN





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